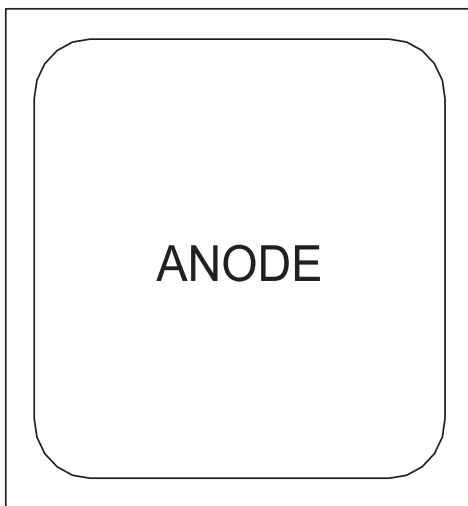


PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	98 x 98 MILS
Die Thickness	10.6 MILS
Anode Bonding Pad Area	82.5 x 82.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 4 INCH WAFER

1,170

PRINCIPAL DEVICE TYPES

CR6AF1GPP Series

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R1 (1-August 2002)

The Typical Electrical Characteristics data
for this chip is currently being revised.

For the latest updated data for this Chip Process,
please visit our website at:

www.centrasemi.com/chip

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R1 (1-August 2002)